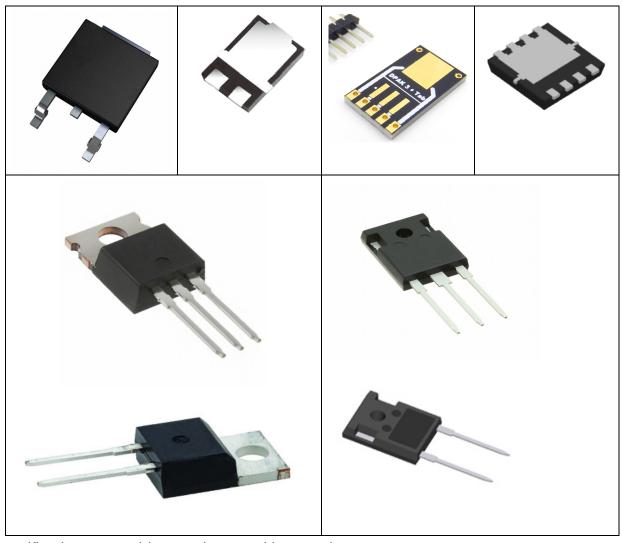


Schottky Diodes and MOSFETs

Novel SiC Products Selection Guide



Specifications are subject to change without notice.

The data indicated herein describe types of components and shall not be considered as assured characteristics.

The products listed in this catalog are not recommended for use in life support systems where a failure or malfunction of the component may directly threaten life or cause injury.

The user of products in such applications shall assume all risks of such use and will agree to hold Bruckewell Technology Co LTD and all the companies whose products are represented in this catalog, harmless against all damages.

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Schottky Diodes and MOSFETs

In the recent decades, the Silicon carbide (SiC), turned out to be an excellent semiconductor material. Composed of carbon and silicon, and used in power applications in which it showed excellent performance, far superior to those of silicon.

Significant progress has been made in the field of the semiconductor industry, in which the technologies for the processing of silicon carbide have become increasingly more sophisticated, and have produced semiconductor devices with excellent performance.

In the facts those devices during the applications have shown a remarkable capacity to reduce losses and a high switching speed in comparison to that offered by silicon. The use of silicon carbide (SiC) as a semiconductor begins to expand into multiple applications and always proves to be more and more the candidate to replace silicon in the most important applications such as automotive and E-Bike motor control.

For these reasons, Bruckewell Semi decided to launch the production of the SiC Products, including the SiC Schottky Diode and SiC MOSFET, support the 650V to 1200V, and give the opportunity to its customers to take advantage of the benefits that the products offer in the SiC high-voltage power applications.

Present our SiC products line as below

SMD Package								
Amp	DFN3X3	DFN5X6	TO-277	DFN 8X8	TO-252(DPak)	TO-263(D2Pak)		
4					CBR04P65D			
6				CBR06P65HL	CBR06P65D			
8				CBR08P65HL	CBR08P65D			
10	ODD4 ODOSLIM		CBR10P65S	CBR10P65HL	CBR10P65D			
	CBR10P65HM		CBR10120S		CBR10120D			
20			CBR20120S					
30		CBR30120H	CBR30120S					
40								

DFN 3X3 is unique package and CBR10P65HM is first smallest SiC SBD Diode in the industry.

TO-277 has same foot print with TO-252 (DPak), and has better thermal performance.

Through Hole Package								
Amp	TO-220AC	TO-220AB	TO-247	TO-247 (Dual Die)				
4	CBR04P65							
6	CBR06P65							
8	CBR08P65							
10	CBR10P65		CBR10120W					
10	CBR10120	CBR10120P	CDR1012000					
20	CBR20P65	CBR20P65PC	CBR20P65W	CBR20P65WC				
20	CBR20120	CBR20120P	CBR20120W	CBR20120WC				
30			CBR30120W					
40				CBR40P65WC				
40				CBR40120WC				



Schottky Diodes and MOSFETs

Part Nomenclature								
Example: CBR20P65PC								
CBR	SiC Barrier Rectifier							
CMS	SiC MOSFET							
20	IF, Forward current, as 20A							
P65	Breakdown Voltage, as P65=650V, 120=1200V							
	Package Code							
	Blank: TO-220AC-2L							
	P: TO-220AB							
	PC: TO-220AB, Dual Die							
	D: TO-252-2L, DPAK							
	W: TO-247-2L							
PC	WC: TO-247-3L, Dual Die							
PC	WU: TO-247-3L, Single Die							
	S: TO-277							
	A: SMA, B: SMB, C: SMC							
	B: TO-263, D2PAK							
	H: DFN5x6							
	HM: DFN3x3							
	HL: DFN8x8							

When the diodes are used simultaneously:

 Δ Tj(diode1) = P(diode1) x Rth(j-c) (per diode) + P(diode2) x Rth(c)

To evaluate the conduction losses use the following equation:

 $P = 1.35 \times IF(AV) + 0.144 \times IF2(RMS)$



Schottky Diodes and MOSFETs

4mp	Bruckewell		ST-M	Micro	Infineon	
	TO-220AC	TO-220AB	TO-220AC	TO-220AB	TO-220AC	TO-220AE
2					IDH02G65C5	
2					IDH02G120C5	
3					IDH03SG60C	
3					IDH03G65C5	
4	CDD04D65				IDH04SG60C	
4	CBR04P65				IDH04G65C5	
					IDH05SG60C	
5					IDH05G65C5	
					IDH05G120C5	
6	CBR06P65			STPSC6TH13TI	IDH06SG60C	
6					IDH06G65C5	
	CBR08P65			STPSC8TH13TI STPSC8H065C	IDH08SG60C	
8		CBR08P65			IDH08G65C5	
				3173000000	IDH08G120C5	
9					IDH09SG60C	
9					IDH09G65C5	
	CBR10P65		STPSC10H065D	STPSC10TH13TI	IDH10SG60C	
10	CBR10120	CBR10120P	STPSC10H003D	51750101111311	IDH10G65C5	
	CBN10120	CDN10120F	317301011120		IDH10G120C5	
12			STPSC12065	STPSC12H065C	IDH12SG60C	
14			STPSC1206		IDH12G65C5	
15			STPSC15H12			
				0.00040110050	IDH16G65C5	
16				STPSC16H065C	IDH16G120C5	
00	CBR20P65	CBR20P65PC	STPSC20065D	STPSC20H065C	IDH20G65C5	
20	CBR20120	CBR20120P	STPSC20H12D		IDH20G120C5	

Note:

The suffix C5 in the Infineon Parts means the CoolSiC $^{\text{\tiny{TM}}}$ 5G, others are CoolSiC $^{\text{\tiny{TM}}}$ 3G



Schottky Diodes and MOSFETs

Comparison with Japan suppliers-TO-220AC/AB								
Am p	Bruckewell		Rohm		Toshiba			
	TO-220AC	TO-220AB	TO-220AC	ITO-220AC	TO-220AC	ITO-220AC		
4	CBR04P65		SCS304AP		TRS4E65F	TRS4A65F		
5			SCS205KG					
	CBR06P65		SCS306AP	000000	TRS6E65F	TRS6A65F		
6			SCS206AG	SCS206AM				
8	CBR08P65		SCS308AP	SCS208AM	TRS8E65F	TRS8A65F		
0			SCS208AG					
	CBR10P65 CBR10120		SCS310AP	SCS210AM	TRS10E65F	TRS10A65F		
10		CBR10120P	SCS210AG					
		CBR10120P	SCS210KG					
12			SCS212AG	SCS212AM				
15			SCS215AG	SCS215AM				
			SCS215KG	303213AW				
20	CBR20P65	CBR20P65PC	SCS220AG	SCS330AM				
20	CBR20120	CBR20120P	SCS220KG	SCS220AM				

Note:

The suffix of Rohm Parts means the breakdown voltage, A means 650V, K means 1200V



Schottky Diodes and MOSFETs

Com	Comparison with industry supplier-TO-247 Single/ Dual Die							
Amp	Bruckewell		ST-Micro		Infineon			
	TO-247	TO-247 Dual	TO-247	TO-247 Dual	TO-247	TO-247 Dual		
10	CBR10120W				IDW10G65C5	IDW10G120C5B		
20	CBR20P65W CBR20120W	CBR20P65WC CBR20120WC	STPSC20065W	STPSC20H06 5CW	IDW20G65C5	IDW20G65C5B IDW20G120C5B		
12					IDW12G65C5			
15						IDW15G120C5B		
16					IDW16G65C5			
24						IDW24G65C5B		
30	CBR30120W				IDW30G65C5	IDW30G120C5B		
32						IDW32G65C5B		
40	CBR40120WC		STPSC40065	IDW4000F0F	IDW40G65C5B			
40		CBR40120WC		CW	IDW40G65C5	IDW40G120C5B		

Comp	Comparison with Japan suppliers-TO-247 Single/ Dual Die						
Amp	Bruckewell		Rohm		Fuji electric		
	TO-247	TO-247 Dual	TO-247	TO-247 Dual	TO-247	TO-247 Dual	
10	CBR10120W			SCS210KE2	FDCY10S65		
15			SCS215AE				
20	CBR20P65W	CBR20P65WC	00000045	SCS220AE2	FDCY18S120	FDCY20C65	
20	CBR20120W	CBR20120WC	SCS220AE	SCS220KE2			
25					FDCY25S65		
20	CBR30120W	000000000			SCS230AE2		
30				SCS230KE2			
40		CDD40400WC		SCS240AE2		EDCV26C120	
40		CBR40120WC		SCS240KE2		FDCY36C120	
50						FDCY50C65	



Schottky Diodes and MOSFETs

Product	IO(A)	VB min (V)	VF typ(V)	IR Max (uA)	Package	Number of Diodes
CBR04P65	4	650	1.5	10	TO-220AC	1
CBR04P65D	4	650	1.5	10	DPAK (TO-252)	1
CBR06P65	6	650	1.5	10	TO-220AC	1
CBR06P65D	6	650	1.5	10	DPAK (TO-252)	1
CBR06P65HL	6	650	1.5	10	DFN 8X8	1
CBR08P65	8	650	1.5	10	TO-220AC	1
CBR08P65D	8	650	1.5	10	DPAK (TO-252)	1
CBR08P65HL	8	650	1.5	10	DFN 8X8	1
CBR10P65	10	650	1.5	10	TO-220AC	1
CBR10P65D	10	650	1.5	10	DPAK (TO-252)	1
CBR10P65S	10	650	1.5	10	TO-277	1
CBR10P65HM	10	650	1.5	10	DFN3.3	1
CBR10P65HL	10	650	1.5	10	DFN8X8	1
CBR20P65PC	20	650	1.5	10	TO-220AB	2
CBR20P65	20	650	1.5	10	TO-220AC	1
CBR20P65W	20	650	1.5	10	TO-247	1
CBR20P65WC	20	650	1.5	10	TO-247	2
CBR40P65WC	40	650	1.5	10	TO-247	2
CBR10120	10	1200	1.5	10	TO-220AC	1
CBR10120P	10	1200	1.5	10	TO-220AB	1
CBR10120D	10	1200	1.5	10	DPAK (TO-252)	1
CBR10120S	10	1200	1.5	10	TO-277	1
CBR10120W	10	1200	1.5	10	TO-247	1
CBR20120WC	20	1200	1.5	10	TO-247	2
CBR20120W	20	1200	1.5	10	TO-247	1
CBR20120	20	1200	1.5	10	TO-220AC	1
CBR20120P	20	1200	1.5	10	TO-220AB	1
CBR20120PC	20	1200	1.5	10	TO-220AB	2
CBR20120S	20	1200	1.5	10	TO-277	1
CBR30120W	30	1200	1.5	10	TO-247	1
CBR30120S	30	1200	1.5	10	TO-277	1
CBR30120H	30	1200	1.5	10	DFN 5X6	1
CBR40120WC	40	1200	1.5	10	TO-247	2



Schottky Diodes and MOSFETs

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